

Title (en)

METHOD OF PERFORMING PLASMA WARM-UP ON SEMICONDUCTOR WAFERS

Title (de)

VERFAHREN ZUR PLASMA-ERWÄRMUNG VON HALBLEITERSCHEIBEN

Title (fr)

PROCEDE DE RECHAUFFEMENT AU PLASMA DE PLAQUETTES SEMI-CONDUCTRICES

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Application

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Abstract (en)

[origin: WO0152310A1] A method for stabilizing the temperature of a semiconductor wafer. In one embodiment, the present invention introduces a semiconductor wafer into an processing environment. Prior to subjecting said semiconductor wafer to a conventional semiconductor process, the present invention performs a plasma warm-up step. The aforementioned plasma warm-up step of the present invention is comprised of the following steps. First, the present invention subjects the semiconductor wafer to an inert gas plasma within the processing environment. Next, the present invention continues to subject the semiconductor wafer to the inert gas plasma until the semiconductor wafer achieves a desired temperature.

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